

Hema C P Movva

List of Publications by Year in descending order

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304602

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42
docs citations

42
times ranked

4741
citing authors

#	ARTICLE	IF	CITATIONS
1	Visualization of Local Conductance in MoS ₂ /WSe ₂ Heterostructure Transistors. Nano Letters, 2019, 19, 1976-1981.	4.5	36
2	Tunable \hat{I} Valley Populations in Hole-Doped Trilayer WSe_2 Physical Review Letters, 2018, 120, 107703.	2.9	23
3	Accelerated carrier recombination by grain boundary/edge defects in MBE grown transition metal dichalcogenides. APL Materials, 2018, 6, .	2.2	25
4	High density nonmagnetic cobalt in thin films. Nanotechnology, 2018, 29, 195703.	1.3	8
5	Spin-Conserving Resonant Tunneling in Twist-Controlled WSe ₂ -hBN-WSe ₂ Heterostructures. Nano Letters, 2018, 18, 5967-5973.	4.5	29
6	Evidence of Formation of Superdense Nonmagnetic Cobalt. Scientific Reports, 2017, 7, 41856.	1.6	10
7	Reconfigurable Complementary Monolayer MoTe ₂ Field-Effect Transistors for Integrated Circuits. ACS Nano, 2017, 11, 4832-4839.	7.3	108
8	Angular dependence of magnetization reversal in epitaxial chromium telluride thin films with perpendicular magnetic anisotropy. Journal of Magnetism and Magnetic Materials, 2017, 437, 72-77.	1.0	21
9	Intra-domain periodic defects in monolayer MoS ₂ . Applied Physics Letters, 2017, 110, .	1.5	16
10	Defect passivation of transition metal dichalcogenides via a charge transfer van der Waals interface. Science Advances, 2017, 3, e1701661.	4.7	95
11	Interlayer tunnel field-effect transistor (ITFET): physics, fabrication and applications. Journal Physics D: Applied Physics, 2017, 50, 383002.	1.3	11
12	Versatile Large-Area Custom-Feature van der Waals Epitaxy of Topological Insulators. ACS Nano, 2017, 11, 7457-7467.	7.3	6
13	Density-Dependent Quantum Hall States and Zeeman Splitting in Monolayer and Bilayer WSe_2 Physical Review Letters, 2017, 118, 247701.	2.9	72
14	ReS ₂ -based interlayer tunnel field effect transistor. Journal of Applied Physics, 2017, 122, .	1.1	7
15	Influence of electron-beam lithography exposure current level on the transport characteristics of graphene field effect transistors. Journal of Applied Physics, 2016, 119, .	1.1	14
16	Weak antilocalization and universal conductance fluctuations in bismuth telluro-sulfide topological insulators. Journal of Applied Physics, 2016, 119, .	1.1	17
17	Insights into interlayer tunnel FET performance improvement: Lessons learned from graphene hexagonal boron nitride heterostructures. , 2016, , .		1
18	Room temperature gate-tunable negative differential resistance in MoS ₂ /hBN/WSe ₂ heterostructures. , 2016, , .		10

#	ARTICLE	IF	CITATIONS
19	Shubnikova, de Haas Oscillations of High-Mobility Holes in Monolayer and Bilayer WS_2 Landau Level Degeneracy, Effective Mass, and Negative Compressibility. Physical Review Letters, 2016, 116, 086601.		
20	Effects of Electrode Layer Band Structure on the Performance of Multilayer Graphene-hBN Graphene Interlayer Tunnel Field Effect Transistors. Nano Letters, 2016, 16, 4975-4981.	4.5	28
21	van der Waals Heterostructures with High Accuracy Rotational Alignment. Nano Letters, 2016, 16, 1989-1995.	4.5	477
22	Structural and Electrical Properties of $MoTe_2$ and $MoSe_2$ Grown by Molecular Beam Epitaxy. ACS Applied Materials & Interfaces, 2016, 8, 7396-7402.	4.0	189
23	Top-gated WS_2 field-effect transistors with Pt contacts. , 2015, , .		1
24	Interfacial-oxygen-vacancy mediated doping of MoS_2 by high- κ dielectrics. , 2015, , .		12
25	Top-gated chemical vapor deposited MoS_2 field-effect transistors on Si_3N_4 substrates. Applied Physics Letters, 2015, 106, .	1.5	74
26	Bilayer Graphene-Hexagonal Boron Nitride Heterostructure Negative Differential Resistance Interlayer Tunnel FET. IEEE Electron Device Letters, 2015, 36, 405-407.	2.2	50
27	Air Stable Doping and Intrinsic Mobility Enhancement in Monolayer Molybdenum Disulfide by Amorphous Titanium Suboxide Encapsulation. Nano Letters, 2015, 15, 4329-4336.	4.5	167
28	In Situ Observation of Initial Stage in Dielectric Growth and Deposition of Ultrahigh Nucleation Density Dielectric on Two-Dimensional Surfaces. Nano Letters, 2015, 15, 6626-6633.	4.5	24
29	High-Mobility Holes in Dual-Gated WS_2 Field-Effect Transistors. ACS Nano, 2015, 9, 10402-10410.	7.3	232
30	Gate tunable resonant tunneling in graphene-based heterostructures and device applications. , 2015, , .		2
31	Gate-Tunable Resonant Tunneling in Double Bilayer Graphene Heterostructures. Nano Letters, 2015, 15, 428-433.	4.5	166
32	Strong spin-orbit coupling and Zeeman spin splitting in angle dependent magnetoresistance of Bi_2Te_3 . Applied Physics Letters, 2014, 104, .	1.5	29
33	Impact of contact and access resistances in graphene field-effect transistors on quartz substrates for radio frequency applications. Applied Physics Letters, 2014, 104, .	1.5	4
34	Poly(methyl methacrylate) as a self-assembled gate dielectric for graphene field-effect transistors. Applied Physics Letters, 2014, 104, .	1.5	8
35	Two-dimensional weak anti-localization in Bi_2Te_3 thin film grown on $Si(111)-(7 \times 7)$ surface by molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	72
36	(Invited) Novel Graphene Devices. ECS Transactions, 2013, 58, 73-77.	0.3	0

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37	Theory and synthesis of bilayer graphene intercalated with ICl and IBr for low power device applications. Journal of Applied Physics, 2013, 114, .	1.1	7
38	Three-Gigahertz Graphene Frequency Doubler on Quartz Operating Beyond the Transit Frequency. IEEE Nanotechnology Magazine, 2012, 11, 877-883.	1.1	61
39	Graphene field-effect transistors with self-aligned spin-on-doping of source/drain access regions. , 2012, , .		0
40	Self-aligned graphene field-effect transistors with polyethyleneimine doped source/drain access regions. Applied Physics Letters, 2012, 101, .	1.5	25
41	CMOS-Compatible Synthesis of Large-Area, High-Mobility Graphene by Chemical Vapor Deposition of Acetylene on Cobalt Thin Films. ACS Nano, 2011, 5, 7198-7204.	7.3	109
42	Graphene field-effect transistors using large-area monolayer graphene grown by chemical vapor deposition on Co thin films. , 2011, , .		2